

## ABSTRACT

A semiconductor laser device having a waveguide constructed in a stack of layers including, on a substrate (101) transparent and having a refractive index  $n_s$  for laser light, a first clad layer (103) of a refractive index  $n_{c1}$ , a second clad layer (104) of a refractive index  $n_{c2}$ , a third clad layer (105) of a refractive index  $n_{c3}$ , a first conductivity type guide layer (105) of a refractive index  $n_g$ , an active quantum well layer (107), a second conductivity type guide layer (109), a second conductivity type clad layer (110), and a second conductivity type contact layer (111) deposited in this order, wherein the waveguide has an effective refractive index  $n_e$ , and a relationship of  $n_{c2} < (n_{c1}, n_{c3}) < n_e < (n_s, n_g)$  is satisfied.